

# Silicon Carbide Schottky Barrier Diode



#### Features

- Temperature Independent Switching Behavior
- High Surge Current Capability
- Positive Temperature Coefficient on VF
- Low Conduction Loss
- Zero Reverse Recovery
- High junction temperature 175 °C
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

## **Mechanical Data**

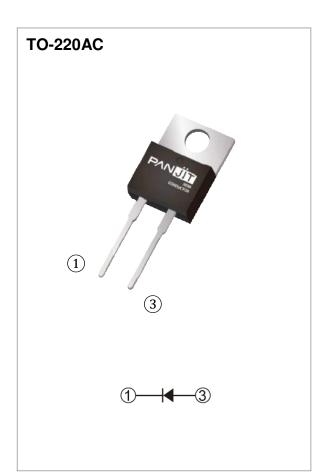
- Case: TO-220AC molded plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.067 ounces, 1.89 grams

## Application

• PFC, UPS, PV Inverter, EV Charging Station, Welder

# Maximum Ratings and Thermal Characteristics (Tc = 25 °C unless otherwise specified)

PARAMETE	SYMBOL	LIMIT	UNITS		
Repetitive Peak Reverse Voltage	VRRM	650	V		
DC Blocking Voltage	V <sub>DC</sub>	650	V		
Continuous Forward Current	Tc= 140 °C	lF	20	А	
Repetitive Peak Surge Current	T <sub>C</sub> = 25 °C , t <sub>p</sub> =10ms		68	A	
Half Sine Wave, D=0.1	$T_C=125 \circ C$ , $t_p=10ms$	IFRM	56		
Peak Forward Surge Current	$T_C= 25 \circ C$ , $t_p = 10 ms$		88	A	
Half Sine Wave	$T_C=125 \circ C$ , $t_p=10ms$		76		
Peak Forward Surge Current $t_p = 10us, Pulse$	IFSM	800	A		
Maximum Power Dissipation	P <sub>total</sub>	153.1	W		
Operating Junction Temperature Ra	TJ	-55~175	٥C		
Storage Temperature Range	Тѕтб	-55~175	٥C		





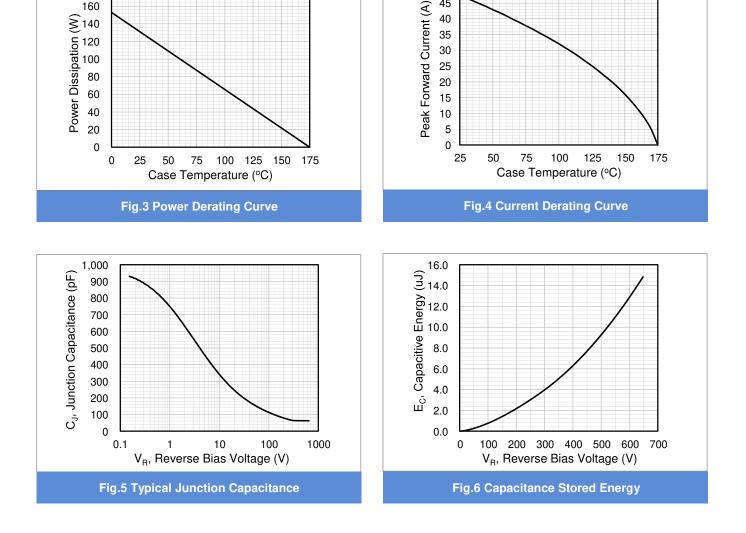
# **Electrical Characteristics** ( $T_c = 25$ °C unless otherwise specified)

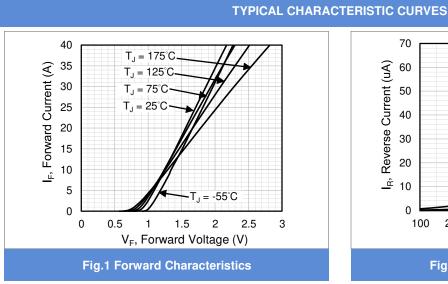
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Forward Voltage Drop	VF	I <sub>F</sub> = 20 A, T <sub>J</sub> = 25 °C	-	1.5	1.7	- V	
		I <sub>F</sub> = 20 A, T <sub>J</sub> = 175 °C	-	1.8	-		
Reverse Leakage Current	IR	V <sub>R</sub> = 650 V, T <sub>J</sub> = 25 °C	-	9	120	μA	
		V <sub>R</sub> = 650 V, T <sub>J</sub> = 175 °C	-	0.062	-	mA	
Total Capacitive Charge	Qc	$I_F = 20 \text{ A}, V_R = 400 \text{V}$	-	43.5	-	nC	
Total Capacitance	С	$V_R = 1V$ , f = 1MHz	-	747	-	pF	
		V <sub>R</sub> = 200V, f = 1MHz	-	77.8	-	pF	
		V <sub>R</sub> = 400V, f = 1MHz	-	63.3	-	pF	
Capacitance Stored Energy	Ec	V <sub>R</sub> = 400V	-	6.8	-	μJ	
Thermal Resistance	Rejc		-	0.98	-	°C/W	

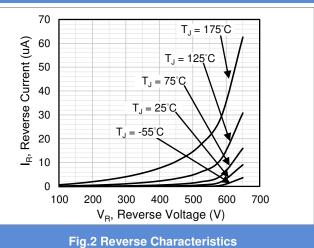
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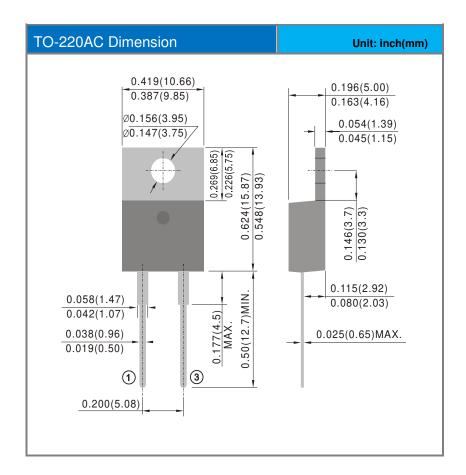
# PCDP2065G1



## **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PCDP2065G1	TO-220AC	50pcs / Tube	CDP2065G1

## **Packaging Information**





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